EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	681	dummy adj capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L2	221	L1 and dram	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L3	277	sram and ferroelectric and @ad<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L4	247	(ferroelectric or high-k sbt pzt) near gate adj (insulator insulating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L5	2520	gate adj dielectric with high-k	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L6	179	dummy adj gate with (periphery peripheral surround surrounding). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L7	57	"4873664" and (dummy inoperable) with (electrode capacitor transistor) and (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17

L8	9528	(MATSUDA-A$ or NAGANO-Y$ OR UEMOTO-Y$ OR FUJII-E$).IN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L9	3	L8 and (dummy inoperable) with transistor not (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L10	9	feram and dram and ferroelectric.detx. and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L11	1	(US-5361234-$).did.	USPAT	OR	OFF	2008/07/17 10:17
L12	4	L8 and (dummy inoperable) with transistor and (ferroelectric or dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L13	7	L12 or L9	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L14	302	dummy adj gate with (periphery peripheral surround surrounding)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L15	1	L11 and boundary adj area with dummy.detx.	USPAT	OR	OFF	2008/07/17 10:17
L16	7324	(257/295,213,296, E21.664,E27.104).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/17 10:17
L17	454	L16 and dummy	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L18	82	L17 and @ad<"19971224"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17

L19	33	L18 not dummy adj (cell word adj line)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L20	762	gate adj (insulator insulating) near3 (ferroelectric or high-k sbt pzt)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L21	2	("5361224" | "5426315").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/17 10:17
L22	66	L16 and dummy adj gate	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L23	6	sram and gate adj (oxide dielectric insulator insulating) near3 ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L24	6	"6320214"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L25	5382	feram dram and ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L26	180	(feram or dram and ferroelectric).detx. and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L27	4	JP-09321248-$ or JP-11251554-$	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17

L28	6	(dish dishing) with dummy with capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L29	76	L26 and (pzt bto sbt strontium near barium near3 (taltalate titanate)). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L30	32	("5959878" "5281555" "5430671") and dummy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L31	5	L6 and @ad<"19971211" and dummy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L32	141	L26 and (capacitor pzt bto sbt strontium near barium near3 (taltalate titanate)). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L33	28	("5959878" "5281555" "5430671") and dummy. detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L34	106	dummy with capacitor with layers and (dummy dummies capacitors cell cells wordline wordlines). detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L35	11	feram and dram and ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17

L36	76	L26 and capacitor.detx. and (pzt bto sbt strontium near barium near3 (taltalate titanate)).detx.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L37	138	gate adj (insulator insulating oxide dielectric) with ferroelectric and @pd<"19971211"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/17 10:17
L38	141	L1 and (ferroelectric perovskite)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17
L39	66	L38 and (dram 1T near3 1C)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/17 10:17

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